

Sub C1
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23. (Amended) A semiconductor substrate having a planarized structure formed according to a method comprising:

- forming a pad on a surface of said substrate;
- forming at least one trench in said substrate;
- applying a filler material by high density plasma method in said at least one trench and on said pad, said filler material filling said at least one trench to a predetermined height;
- selectively removing said filler material on said pad so as to separate said filler material in said at least one trench and said filler material on said surface by an exposed area of said pad, and
- removing said filler material on said pad while allowing said filler material in said at least one trench to remain filled to said predetermined height.

Please add the following new claims:

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- - 24. The semiconductor substrate according to claim 8, wherein said filler material comprises high density plasma oxide.

25. The semiconductor substrate according to claim 8, wherein said at least one trench comprises a wide trench and a narrow trench.

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26. The semiconductor substrate according to claim 8, wherein said filler material comprises non-conformal high density plasma oxide.

27. The semiconductor substrate according to claim 24, wherein said high density plasma oxide comprises silicon dioxide.

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28. The semiconductor substrate according to claim 24, wherein said high density plasma oxide comprises silicon dioxide doped with one of phosphorus, boron and fluorine.

Sub D5

29. The semiconductor substrate according to claim 8, wherein said substrate is formed without chemical mechanical polishing and reactive ion etching.

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30. The semiconductor substrate according to claim 8, wherein said at least one trench comprises shallow trench isolations. - -
